

TOSHIBA Multichip Discrete Device

HN7G05FU

Power Management Switch Applications, Inverter Circuit Applications, Driver Circuit Applications and Interface Circuit Applications

Unit: mm

Q1 (transistor): RN2301 equivalent
 Q2 (MOSFET): 2SK1830 equivalent

Q1 (Transistor) Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-50	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-10	V
Collector current	I _C	-100	mA

Q2 (MOSFET) Absolute Maximum Ratings (Ta = 25°C)

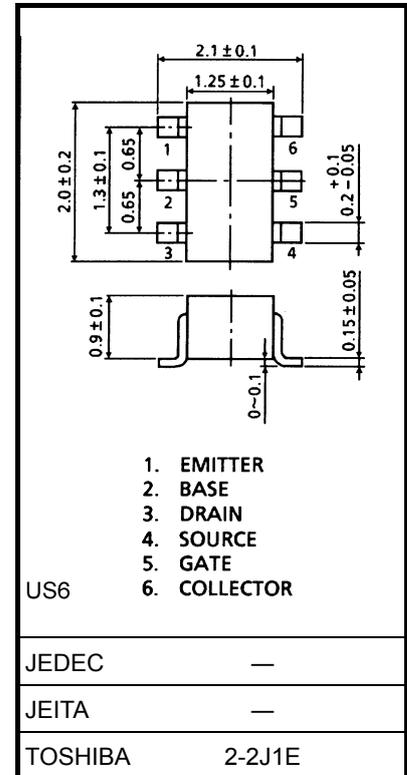
Characteristic	Symbol	Rating	Unit
Drain-source voltage	V _{DS}	20	V
Gate-source voltage	V _{GSS}	10	V
Drain current	I _D	50	mA

Q1, Q2 Common Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Power dissipation	P (Note 1)	200	mW
Junction temperature	T _j	150	°C
Storage temperature range	T _{stg}	-55~150	°C

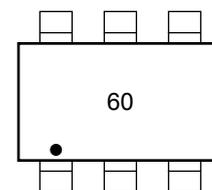
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
 Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Total rating

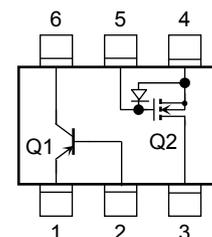


Weight: 0.0068 g (typ.)

Marking



Equivalent Circuit (top view)



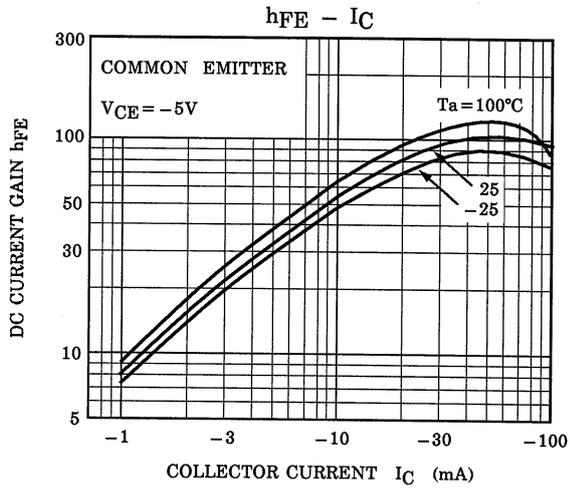
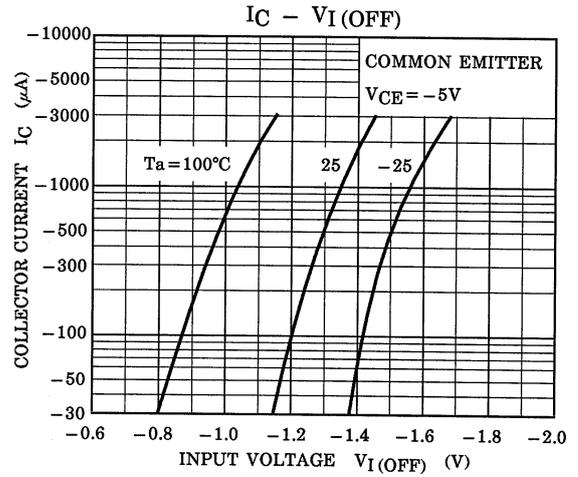
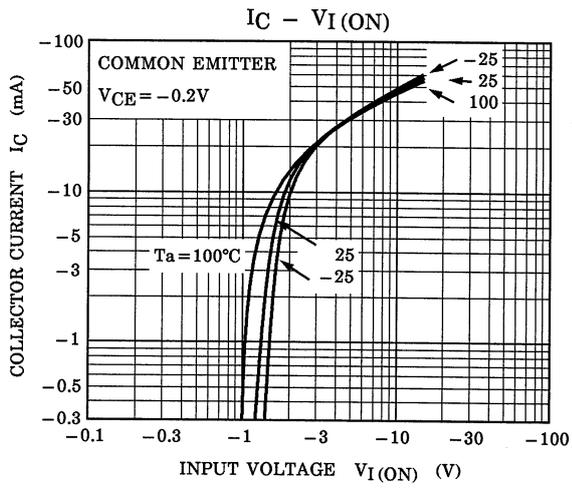
Q1 (Transistor) Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -50\text{ V}, I_E = 0$	—	—	-100	nA
	I_{CEO}	$V_{CE} = -50\text{ V}, I_E = 0$	—	—	-500	nA
Emitter cutoff current	I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$	-0.82	—	-1.52	mA
DC current gain	h_{FE}	$V_{CE} = -5\text{ V}, I_C = -10\text{ mA}$	30	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -5\text{ mA}, I_B = -0.25\text{ mA}$	—	-0.1	-0.3	V
Input voltage (ON)	$V_{I(ON)}$	$V_{CE} = -0.2\text{ V}, I_C = -5\text{ mA}$	-1.1	—	-2.0	V
Input voltage (OFF)	$V_{I(OFF)}$	$V_{CE} = -5\text{ V}, I_C = -0.1\text{ mA}$	-1.0	—	-1.5	V
Input resistor	R1	—	3.29	4.7	6.11	k Ω
Resistor ratio	R1/R2	—	0.9	1.0	1.1	

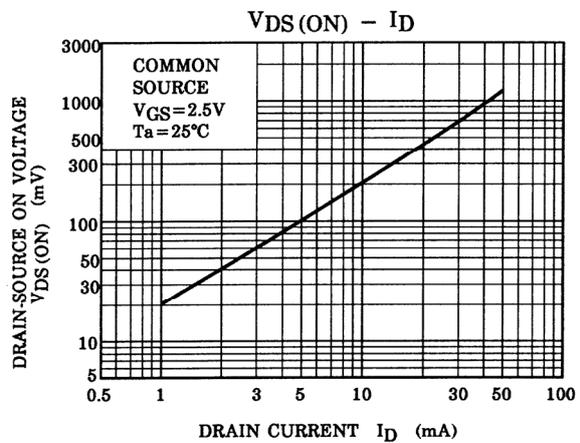
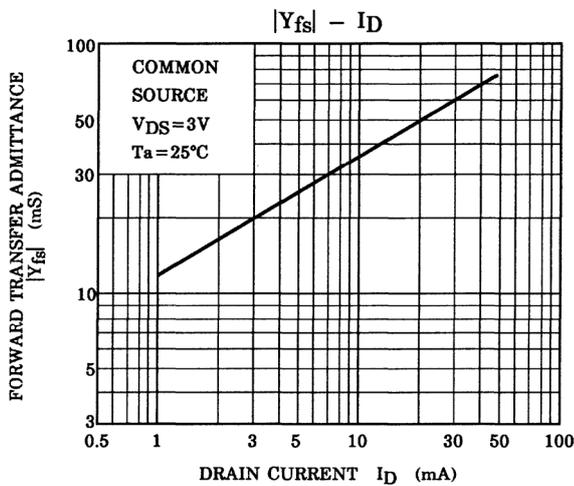
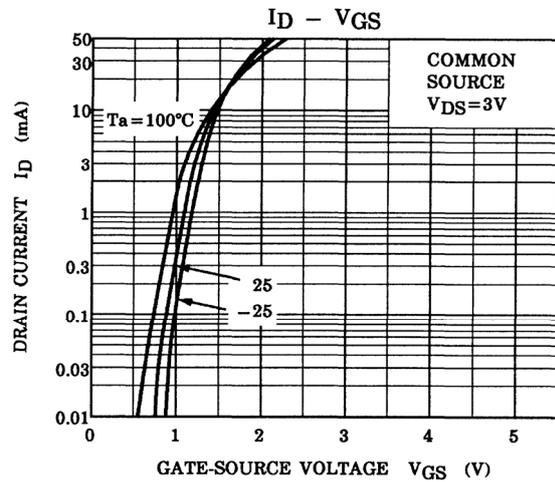
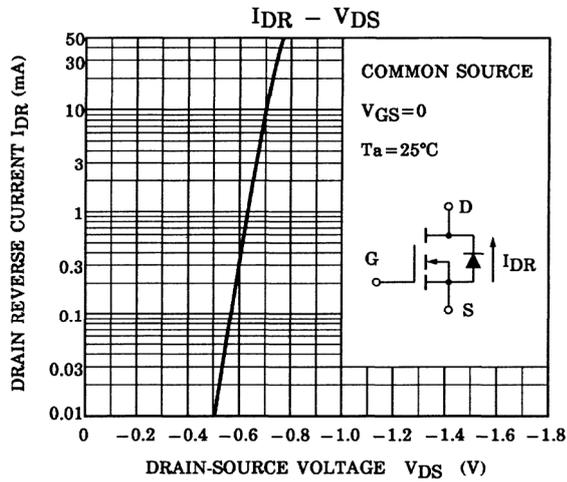
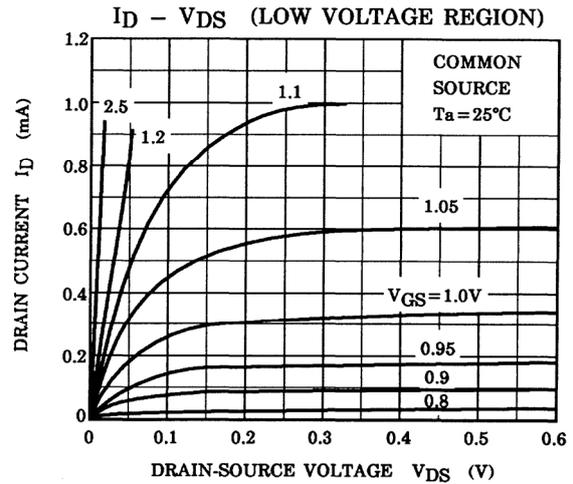
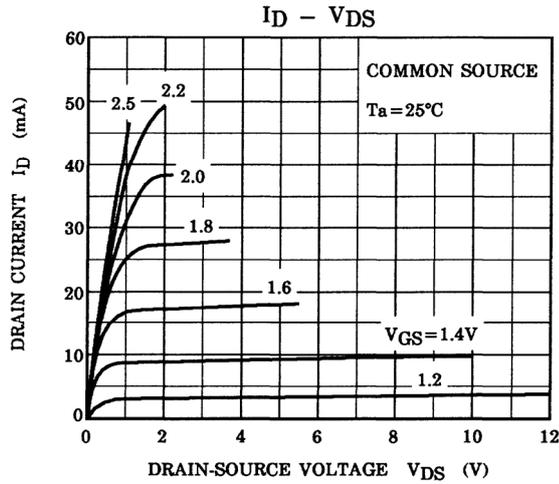
Q2 (MOSFET) Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	$V_{GS} = 10\text{ V}, V_{DS} = 0$	—	—	1	μA
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 100\text{ }\mu\text{A}, V_{GS} = 0$	20	—	—	V
Drain cutoff current	I_{DSS}	$V_{DS} = 20\text{ V}, V_{GS} = 0$	—	—	1	μA
Gate threshold voltage	V_{th}	$V_{DS} = 3\text{ V}, I_D = 0.1\text{ mA}$	0.5	—	1.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 3\text{ V}, I_D = 10\text{ mA}$	20	—	—	mS
Drain-source ON-resistance	$R_{DS(ON)}$	$I_D = 10\text{ mA}, V_{GS} = 2.5\text{ V}$	—	20	40	Ω

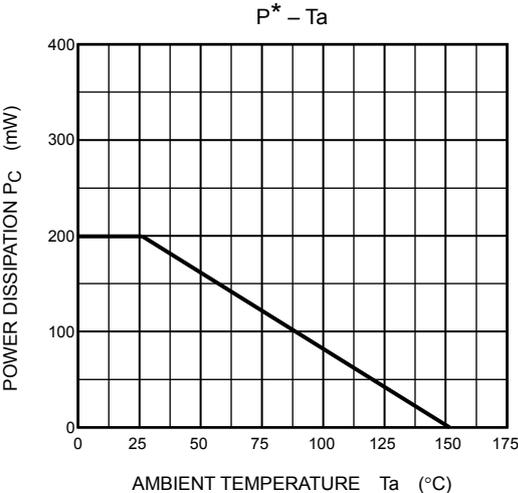
Q1 (Transistor)



Q2 (S-MOS)



Q1, Q2 common



*:Total rating

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20070701-EN GENERAL

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